Supporting Information

Quantum Mechanics Predictions for Contact Resistance of “End-contacted” Metal–Graphene and Metal–Nanotube Interfaces

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Figure S1-1. (a) Partial Density of States (PDOS) of Ti–graphene $I$–$V$ model.
Figure S1-2. Partial Density of States (PDOS) of (b) Pd–graphene and (c) Pt–graphene $I–V$ models.
Figure S1-3. Partial Density of States (PDOS) of (d) Cu–graphene and (e) Au–graphene $I$–$V$ models.
Figure S2. Partial Density of States (PDOS) of p orbital of surface C atoms on graphene.

(a) Ti, (b) Pd, (c) Pt, (d) Cu, and (e) Au I–V models.
Figure S3. Partial Density of States (PDOS) of d orbital of surface metal atoms. (a) Ti, (b) Pd, (c) Pt, (d) Cu, and (e) Au $I-V$ models.
Figure S4. Transmission coefficient ($T(E)$) of (a) Ti, (b) Pd, (c) Pt, (d) Cu, and (e) Au $I$–$V$ models.